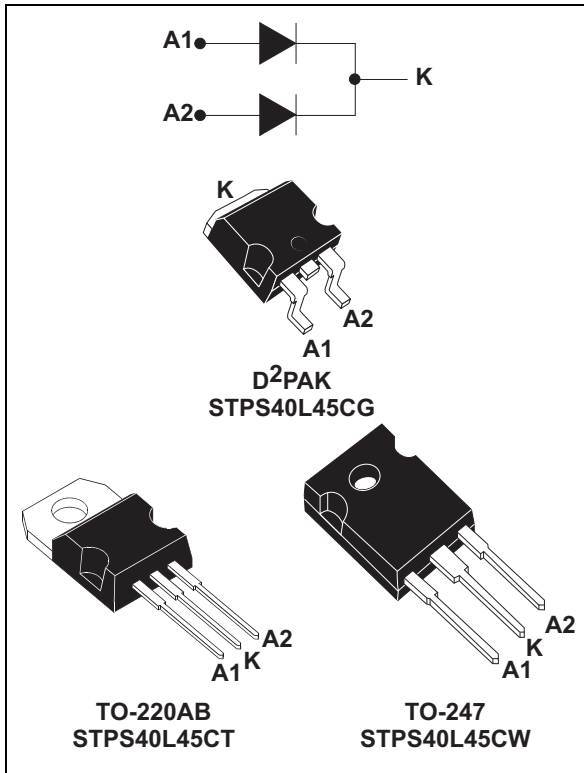


Low drop power Schottky rectifier

Datasheet - production data



Description

Dual center tap Schottky barrier rectifier designed for high frequency switched mode power supplies and DC to DC converters.

Packaged in TO-220AB, TO-247 and D²PAK these devices are intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.

Table 1. Device summary

$I_{F(AV)}$	2 x 20 A
V_{RRM}	45 V
$T_j(\text{max})$	150° C
$V_F(\text{max})$	0.49 V

Features

- Low forward voltage drop meaning very small conduction losses
- Low switching losses allowing high frequency operation
- Avalanche capability specified

1 Characteristics

Table 2. Absolute Ratings (limiting values, per diode)

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive peak reverse voltage		45	V
I _{F(RMS)}	Forward rms current		30	A
I _{F(AV)}	Average forward current	T _c = 130° C δ = 0.5	Per diode 40 Per device	A
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms Sinusoidal	220	A
I _{RRM}	Repetitive peak reverse current	t _p = 2 μs square F = 1 kHz	2	A
I _{RSM}	Non repetitive peak reverse current	t _p = 100 μs square	3	A
P _{ARM}	Repetitive peak avalanche power	t _p = 1 μs T _j = 25° C	8100	W
T _{stg}	Storage temperature range		-65 to + 150	°C
T _j	Maximum operating junction temperature ⁽¹⁾		150	°C
dV/dt	Critical rate of rise of reverse voltage		10000	V/μs

1. $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistances

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case	Per diode	1.5	°C/W
		Total	0.8	
R _{th(c)}	Coupling		0.1	°C/W

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j(\text{diode 1}) = P(\text{diode1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode2}) \times R_{th(c)}$$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25° C	V _R = V _{RRM}			0.6	mA
		T _j = 125° C			140	280	mA
V _F ⁽¹⁾	Forward voltage drop	T _j = 25° C	I _F = 20 A			0.53	V
		T _j = 125° C	I _F = 20 A		0.42	0.49	
		T _j = 25° C	I _F = 40 A			0.69	
		T _j = 125° C	I _F = 40 A		0.6	0.7	

1. Pulse test: t_p = 380 μs, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 0.28 \times I_{F(AV)} + 0.0105 I_{F(RMS)}^2$$

Figure 1. Average forward power dissipation versus average forward current (per diode)

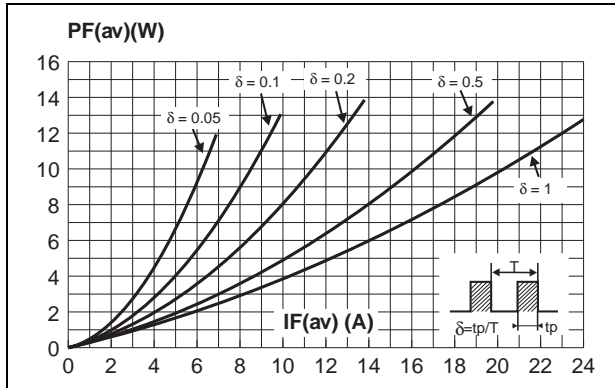


Figure 2. Average forward current versus ambient temperature ($\delta = 0.5$, per diode)

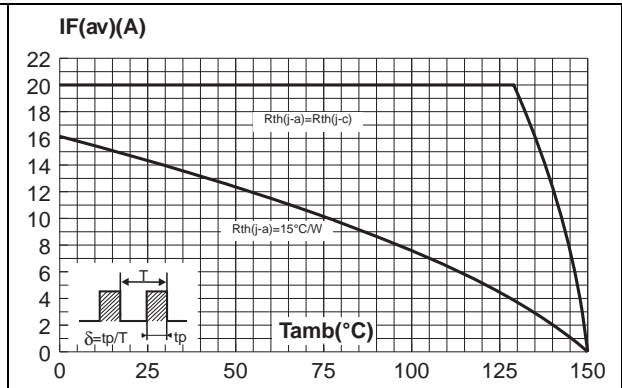


Figure 3. Normalized avalanche power derating versus pulse duration

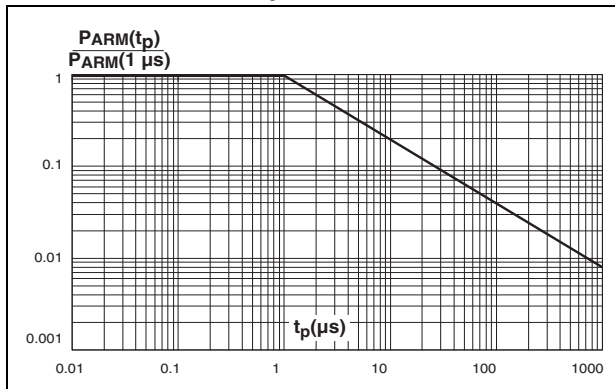


Figure 4. Normalized avalanche power derating versus junction temperature

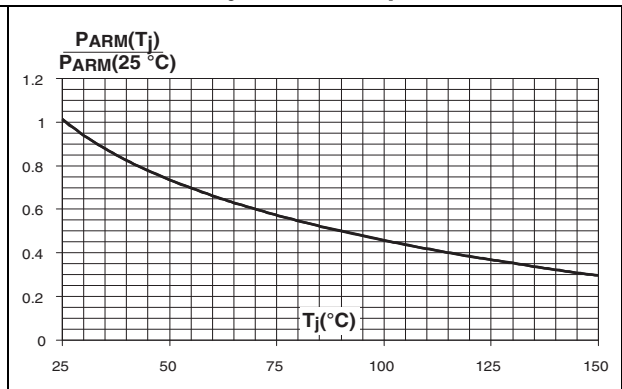


Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

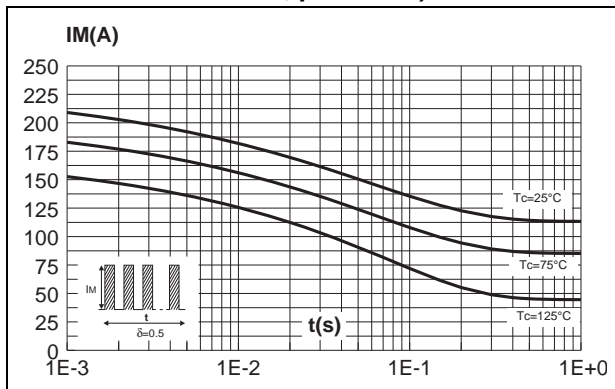


Figure 6. Relative variation of thermal impedance junction to case versus pulse duration

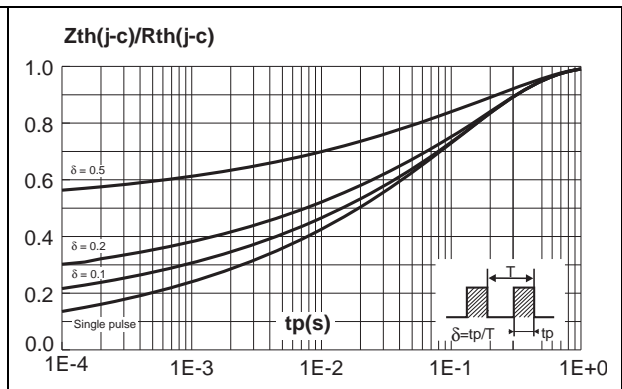


Figure 7. Reverse leakage current versus reverse voltage applied (typical values, per diode)

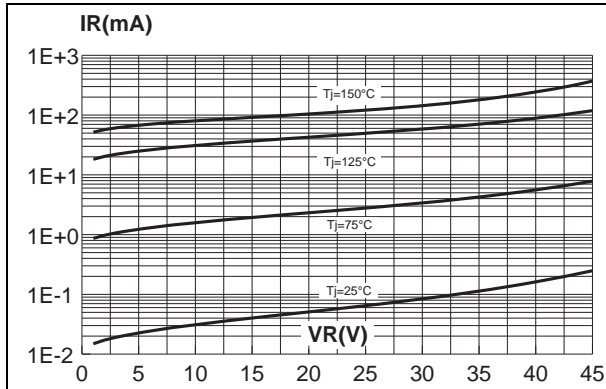


Figure 8. Junction capacitance versus reverse voltage applied (typical values, per diode)

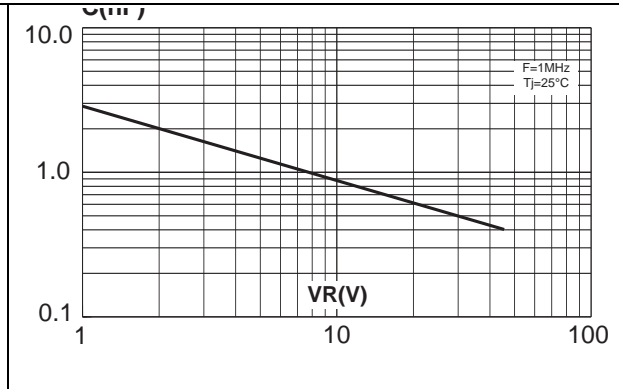


Figure 9. Forward voltage drop versus forward current (maximum values, per diode)

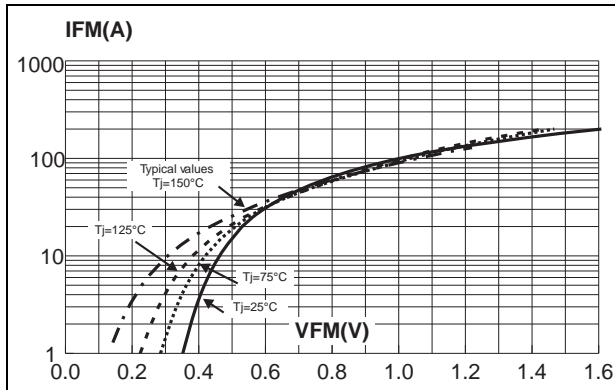


Figure 10. Thermal resistance junction to ambient versus copper surface under tab

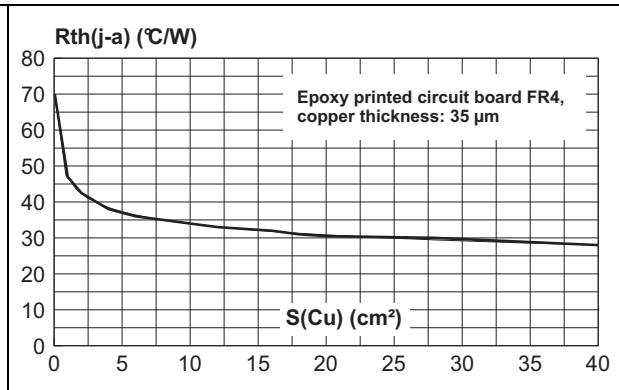


Table 5. TO-220AB dimension values

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.17	0.18
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.045	0.067
c	0.48	0.70	0.019	0.027
D	15.25	15.75	0.60	0.62
D1	1.27 typ.		0.05 typ.	
E	10	10.40	0.39	0.41
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.19	0.20
F	1.23	1.32	0.048	0.052
H1	6.20	6.60	0.24	0.26
J1	2.40	2.72	0.094	0.107
L	13	14	0.51	0.55
L1	3.50	3.93	0.137	0.154
L20	16.40 typ.		0.64 typ.	
L30	28.90 typ.		1.13 typ.	
ØP	3.75	3.85	0.147	0.151
Q	2.65	2.95	0.104	0.116

Figure 12. D²PAK dimension definitions

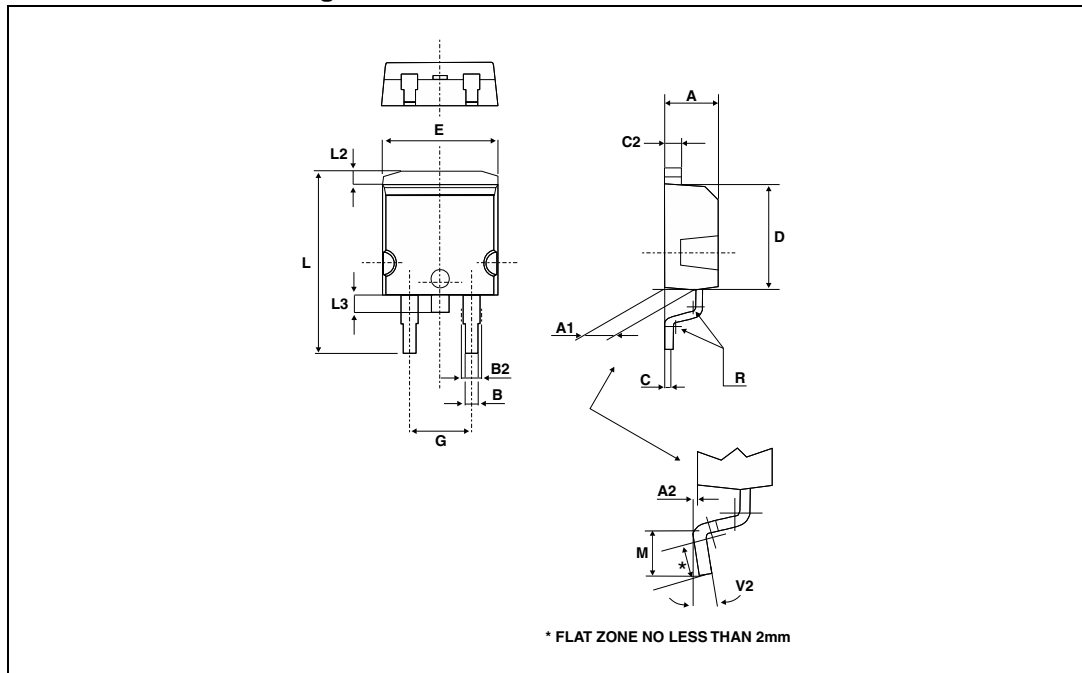


Table 6. D²PAK dimension values

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.30	1.75	0.051	0.069
M	2.29	2.79	0.090	0.110
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

Figure 13. D²PAK footprint (dimensions in mm)

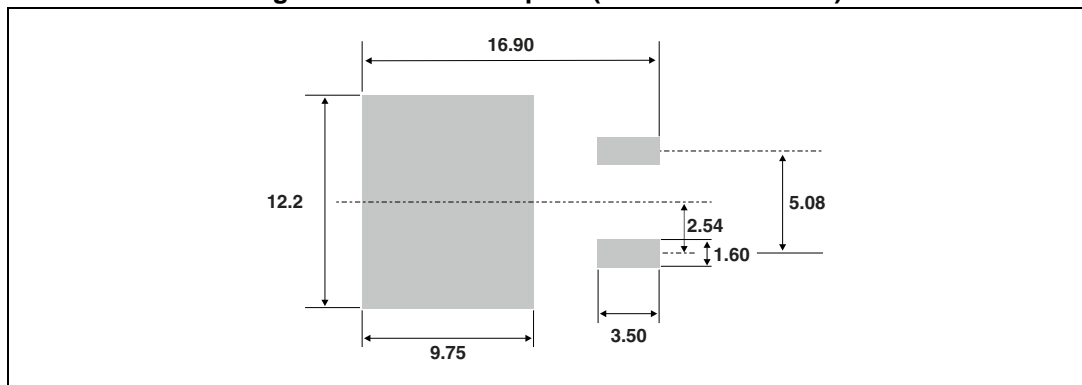


Figure 14. TO-247 dimension definitions

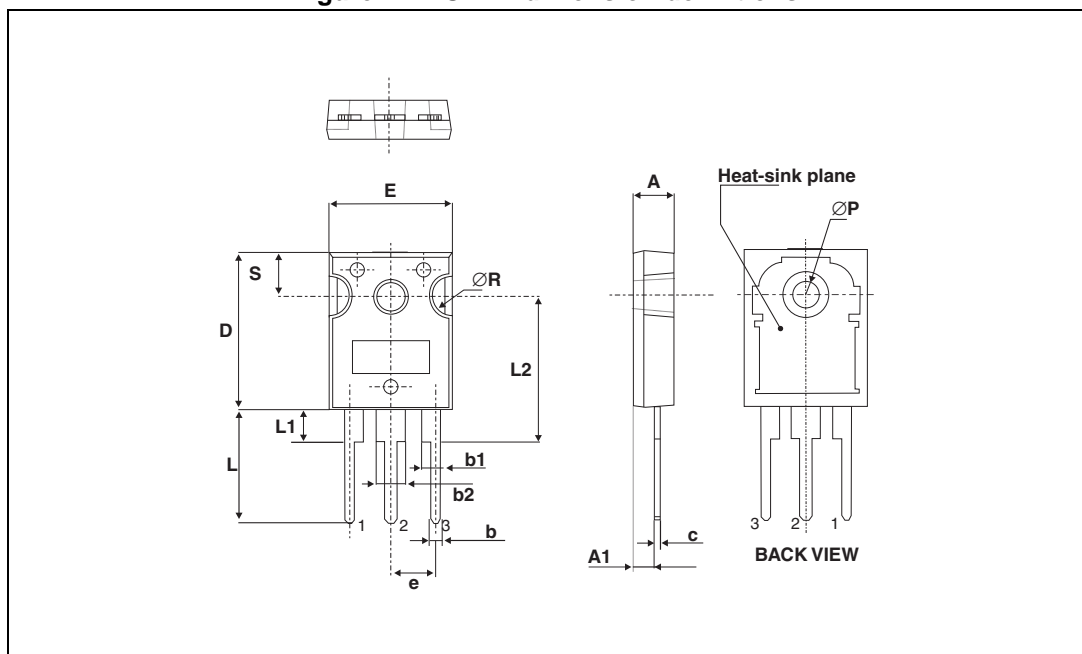


Table 7. TO-247 dimension values

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ	Max.
A	4.85		5.15	0.191		0.203
A1	2.20		2.60	0.086		0.102
b	1.00		1.40	0.039		0.055
b1	2.00		2.40	0.078		0.094
b2	3.00		3.40	0.118		0.133
c	0.40		0.80	0.015		0.031
D ⁽¹⁾	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e	5.30	5.45	5.60	0.209	0.215	0.220
L	14.20		14.80	0.559		0.582
L1	3.70		4.30	0.145		0.169
L2	18.50 typ.			0.728 typ.		
∅P ⁽²⁾	3.55		3.65	0.139		0.143
∅R	4.50		5.50	0.177		0.217
S	5.30	5.50	5.70	0.209	0.216	0.224

1. Dimension D plus gate protrusion does not exceed 20.5 mm
2. Resin thickness around the mounting hole is not less than 0.9 mm

3 Ordering Information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS40L45CG	STPS40L45CG	D ² PAK	1.8g	500	Tape and reel
STPS40L45CT	STPS40L45CT	TO-220AB	2g	50	Tube
STPS40L45CW	STPS40L45CW	TO-247	4.4g	30	Tube

4 Revision history

Table 9. Document revision history

Date	Revision	Description of Changes
Jul-2003	4A	Previous version
30-Oct-2013	5	Updated Package information section

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